

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of fabricating a device using a lithographic process, the method comprising:

applying a first layer of conductive material to an upper surface of a resist layer on a substrate;

providing a second layer of conductive material on a lower surface of the resist layer, between the resist layer and the substrate;

exposing a part of a the resist layer ~~on a substrate~~ to ultraviolet radiation; and

applying an electric field across the resist layer by applying a potential difference between the two conducting layers, the direction of the field being substantially perpendicular to a plane of the resist layer during the exposing.

2. (Canceled).

3. (Canceled).

4. (Currently Amended) A method according to claim 2 1, wherein said conductive material of at least one of the layers is metallic.

5. (Original) A method according to claim 4, further comprising applying said layer of conductive material to a thickness of less than 50nm.

6. (Currently Amended) A method according to claim 2, wherein at least one of said ~~layer~~ layers of conductive material overlaps a side or base of the device.

7. (Canceled).

8. (Currently Amended) A method according to claim 7 6, wherein ~~said layer~~ both layers of conductive material ~~overlaps a~~ overlap the side or base of the device.

9. (Canceled).

10. (Canceled).

11. (Canceled).

12. (Original) A method according to claim 1, wherein said radiation is in the extreme ultra-violet range.

13. (Previously Presented) A method according to claim 1, further comprising orienting the electric field such that an upper surface of the resist layer is at a positive potential with respect to a lower surface.

14. (Currently Amended) A lithographic apparatus comprising:  
an illumination system configured to condition a projection beam of ultraviolet radiation;  
a support structure configured to support a patterning device to impart a pattern to the projection beam;  
a substrate table configured to hold a substrate having a resist layer;  
a projection system configured to project the patterned beam onto a target portion of the substrate; and  
an electric field generator configured and arranged to apply ~~an electric field across a resist layer provided on a surface of said substrate~~ a potential difference between a layer of conductive material on an upper surface of the resist layer and a layer of conductive material on a lower surface of the resist layer, between the resist layer and the substrate, the direction of said field being substantially perpendicular to the plane of the resist layer.

15. (Previously Presented) A method of fabricating a device using a lithographic process, comprising:

applying a radiation sensitive resist on top of the device, the resist material incorporating a conductive material; and

exposing a part of the resist to ultraviolet radiation while applying an electric field across the resist.

16. (Currently Amended) A method of processing a device using a lithographic process, said device comprising a radiation sensitive and conductive resist material, said method comprising:

exposing the conductive resist material to UV radiation while applying an electric field across the resist material by directly coupling the conductive resist material to a fixed potential.

17. (Currently Amended) The apparatus of claim 14, wherein the electric field generator is further configured to apply said electric field by connecting a the layer of conductive material on ~~an~~ the upper surface of the resist layer to a fixed potential.

18. (Canceled).

19. (Previously Presented) The apparatus of claim 14, wherein said radiation is in the extreme ultra-violet range.

20. (Previously Presented) The method of claim 15, further comprising applying an electric field across the resist by directly coupling the resist to a fixed potential.

21. (Previously Presented) The method of claim 15, wherein said radiation is in the extreme ultra-violet range.

22. (Canceled).

23. (Previously Presented) The method of claim 16, wherein said radiation is in the extreme ultra-violet range.

24. (New) A method of fabricating a device using a lithographic process, the method comprising:

applying a layer of metallic conductive material to an upper surface of a resist layer on a substrate;

exposing a part of the resist layer to ultraviolet radiation; and

applying an electric field across the resist layer, the direction of the field being substantially perpendicular to a plane of the resist layer during the exposing.

25. (New) A method according to claim 24, wherein said electric field is applied by connecting said conductive layer to a fixed potential.

26. (New) A method according to claim 24, further comprising applying said layer of conductive material to a thickness of less than 50nm.

27. (New) A method according to claim 24, wherein said layer of conductive material overlaps a side or base of the device.